



DC COMPONENTS CO., LTD.

DISCRETE SEMICONDUCTORS

2SB857

TECHNICAL SPECIFICATIONS OF PNP EPITAXIAL PLANAR TRANSISTOR

Description

Designed for low frequency power amplifier.

Pinning

- 1 = Base
- 2 = Collector
- 3 = Emitter

Absolute Maximum Ratings($T_A=25^{\circ}\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-70	V
Collector-Emitter Voltage	V_{CE0}	-50	V
Emitter-Base Voltage	V_{EB0}	-5	V
Collector Current (continuous)	I_C	-4	A
Collector Current (peak)	I_C	-8	A
Total Power Dissipation($T_C=25^{\circ}\text{C}$)	P_D	40	W
Junction Temperature	T_J	+150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}\text{C}$

